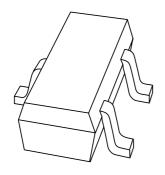
## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# BC856T; BC857T series PNP general purpose transistors

Product data sheet Supersedes data of 1999 Apr 26 2000 Nov 15



## PNP general purpose transistors

BC856T; BC857T series

#### **FEATURES**

• Low current (max. 100 mA)

• Low voltage (max. 65 V).

## **APPLICATIONS**

• General purpose switching and amplification, especially in portable equipment.

## **DESCRIPTION**

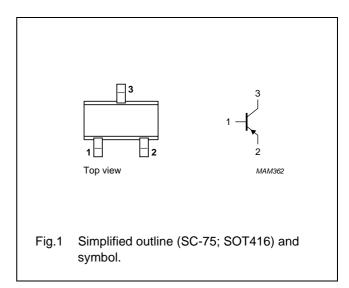
PNP transistor in an SC-75 (SOT416) plastic package. NPN complements: BC846T; BC847T series.

## **MARKING**

TYPE NUMBER	MARKING CODE
BC856AT	3A
BC856BT	3B
BC857AT	3E
BC857BT	3F
BC857CT	3G

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC856AT; BC856BT		_	-80	V
	BC857AT; BC857BT; BC857CT		_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC856AT; BC856BT		_	-65	V
	BC857AT; BC857BT; BC857CT		_	-45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-200	mA
I <sub>BM</sub>	peak base current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	150	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## PNP general purpose transistors

BC856T; BC857T series

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	833	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	_	-15	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-5	μΑ
I <sub>EBO</sub>	emitter cut-off current	$V_{EB} = -5 \text{ V; } I_C = 0$	_	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V; } I_{C} = -2 \text{ mA}$				
	BC856AT; BC857AT		125	_	250	
	BC856BT; BC857BT		220	_	475	
	BC857CT		420	_	800	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-200	mV
	voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	_	_	-400	mV
V <sub>BE</sub>	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-580	_	-700	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	_	_	-770	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V; } f = 1 \text{ MHz; } I_E = i_e = 0$	_	_	2.5	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 \text{ V; } f = 1 \text{ MHz; } I_C = i_c = 0$	_	10	_	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	-	-	MHz
F	noise figure	$I_C = -200 \mu A; V_{CE} = -5 V;$ $R_S = 2 k\Omega; f = 1 kHz; B = 200 Hz$	_	_	10	dB

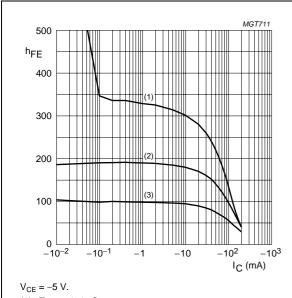
#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

## PNP general purpose transistors

## BC856T; BC857T series

#### **GRAPHICAL INFORMATION BC857AT**

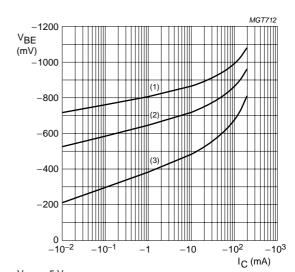


(1)  $T_{amb} = 150 \, ^{\circ}C$ .

(2)  $T_{amb} = 25 \, ^{\circ}C$ .

(3)  $T_{amb} = -55 \,^{\circ}C$ .

Fig.2 DC current gain; typical values.



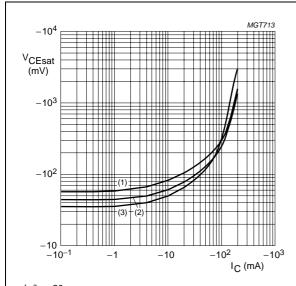
 $V_{CE} = -5 \text{ V}.$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ .

(3) T<sub>amb</sub> = 150 °C.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



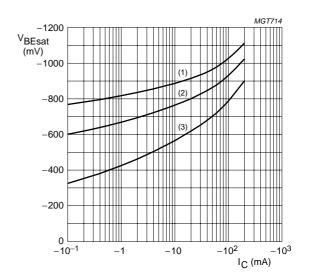
 $I_{\rm C}/I_{\rm B}=20.$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ .

(2)  $T_{amb} = 25 \, ^{\circ}C$ .

(3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

(1)  $T_{amb} = -55 \, ^{\circ}C$ .

(2)  $T_{amb} = 25 \, ^{\circ}C$ .

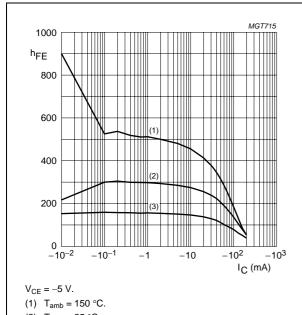
(3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

## PNP general purpose transistors

## BC856T; BC857T series

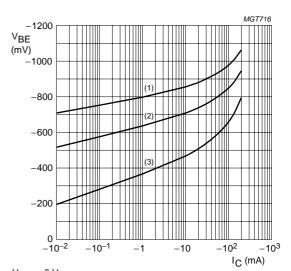
#### **GRAPHICAL INFORMATION BC857BT**



(2)  $T_{amb} = 25 \, ^{\circ}C$ .

(3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.6 DC current gain; typical values.



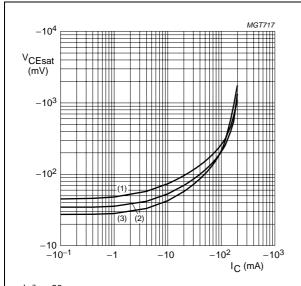
 $V_{CE} = -5 \text{ V}.$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ .

(3) T<sub>amb</sub> = 150 °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.



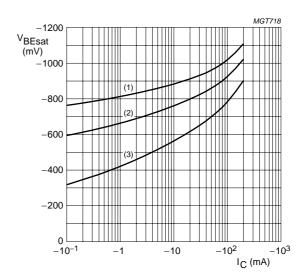
 $I_{\rm C}/I_{\rm B}=20.$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ .

(2)  $T_{amb} = 25 \, ^{\circ}C$ .

(3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

(1)  $T_{amb} = -55 \, ^{\circ}C$ .

(2)  $T_{amb} = 25 \, ^{\circ}C$ .

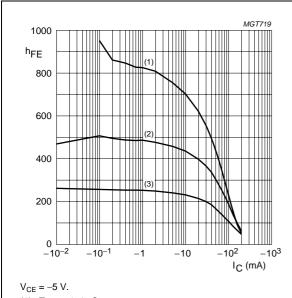
(3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

## PNP general purpose transistors

## BC856T; BC857T series

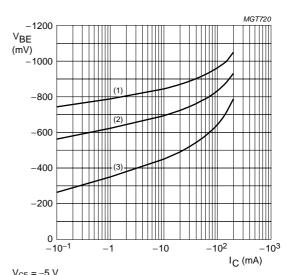
#### **GRAPHICAL INFORMATION BC857CT**



(1)  $T_{amb} = 150 \, ^{\circ}C$ .

- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

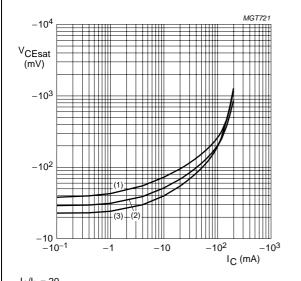
Fig.10 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 25 °C.
- (3) T<sub>amb</sub> = 150 °C.

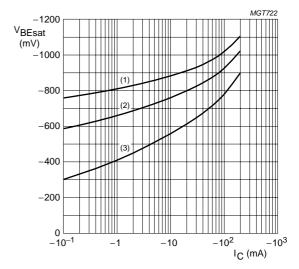
Fig.11 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

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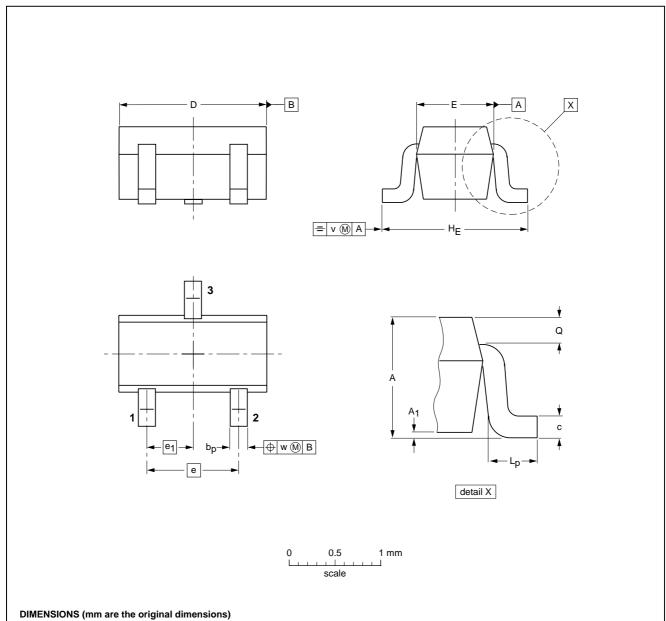
## PNP general purpose transistors

## BC856T; BC857T series

## **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

**SOT416** 



UNIT	Α	max	bp	С	D	E	е	e <sub>1</sub>	HE	L <sub>p</sub>	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT416			SC-75			97-02-28

## PNP general purpose transistors

BC856T; BC857T series

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DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
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Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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